



(19)

(11) Publication number:

05062911 A

Generated Document.

PATENT ABSTRACTS OF JAPAN

(21) Application number: 03223234

(51) Intl. Cl.: H01L 21/205 H01S 3/18

(22) Application date: 04.09.91

(30) Priority:

(43) Date of application
publication: 12.03.93

(84) Designated contracting
states:

(71) Applicant: FUJITSU LTD

(72) Inventor: NAKAI KENYA

(74) Representative:

(54) MANUFACTURE OF
SEMICONDUCTOR
SUPERLATTICE

(57) Abstract:

PURPOSE: To form a Ge layer and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to put a hetero-epitaxial growth method, in which excellent crystal quality and high growth speed can be obtained, into practical use.

CONSTITUTION: The title semiconductor superlattice

manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH₄ and trisilane (Si₃H₈) as raw gas and also using H₂ or inert gas as carrier gas.

COPYRIGHT: (C)1993,JPO&Japio



